60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max T_A = 25°C
60V	8mΩ @ V_{GS} = 10V	14.0A
	12mΩ @ V_{GS} = 4.5V	11.5A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

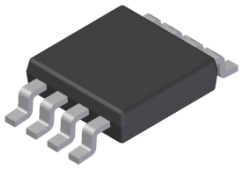
This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance. This device is ideal for use in notebook battery power management and loadswitch.

- Backlighting
- Power Management Functions
- DC-DC Converters

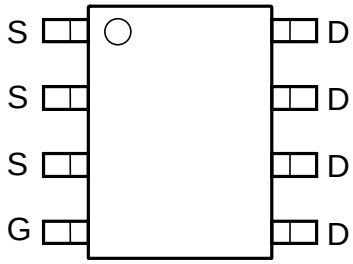
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.074 grams (Approximate)

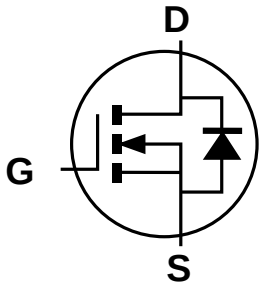
SO-8



Top View



Top View
Internal Schematic



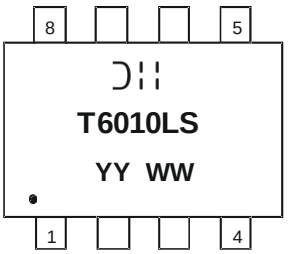
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6010LSS-13	SO-8	2,500/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



= Manufacturer's Marking
T6010LS = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 13 = 2013)
WW = Week (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	14.0 11.0	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	16.7 13.5	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	3	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	80	A
Avalanche Current, L = 0.1mH			I_{AS}	20	A
Avalanche Energy, L = 0.1mH			E_{AS}	20	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	80	°C/W
	t<10s		48	°C/W
Total Power Dissipation (Note 6)		P_D	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	53	°C/W
	t<10s		37	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	6.5	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 48V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.8	—	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	6	8	mΩ	V_{GS} = 10V, I_D = 20A
		—	8	12		V_{GS} = 4.5V, I_D = 20A
Diode Forward Voltage	V_{SD}	—	0.9	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	2,090	—	pF	V_{DS} = 30V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	746	—		
Reverse Transfer Capacitance	C_{rss}	—	38.5	—		
Gate resistance	R_G	—	0.59	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	19.3	—	nC	V_{DS} = 30V, I_D = 20A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	41.3	—		
Gate-Source Charge	Q_{gs}	—	6.0	—		
Gate-Drain Charge	Q_{gd}	—	8.8	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.7	—	ns	V_{DD} = 30V, V_{GS} = 10V, I_D = 20A, R_G = 3Ω
Turn-On Rise Time	t_R	—	4.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	23.4	—		
Turn-Off Fall Time	t_F	—	9.7	—		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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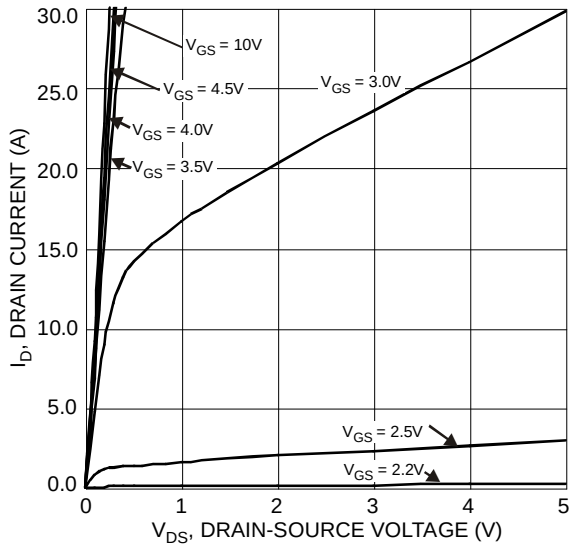


Figure 1 Typical Output Characteristic

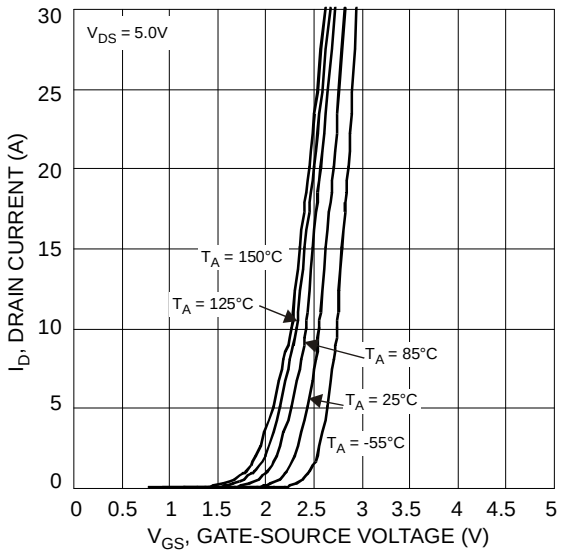


Figure 2 Typical Transfer Characteristics

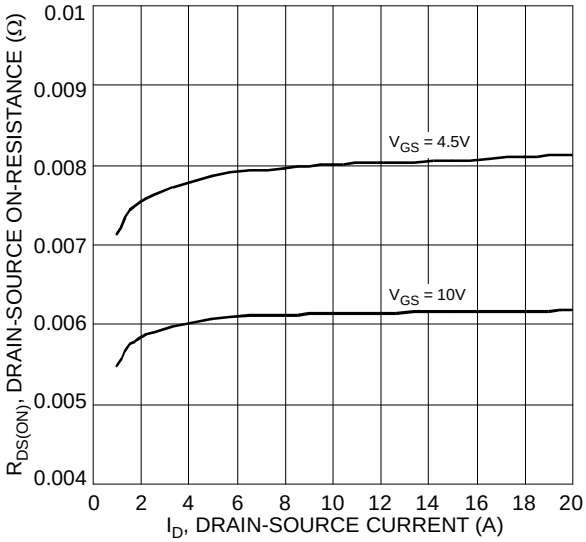


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

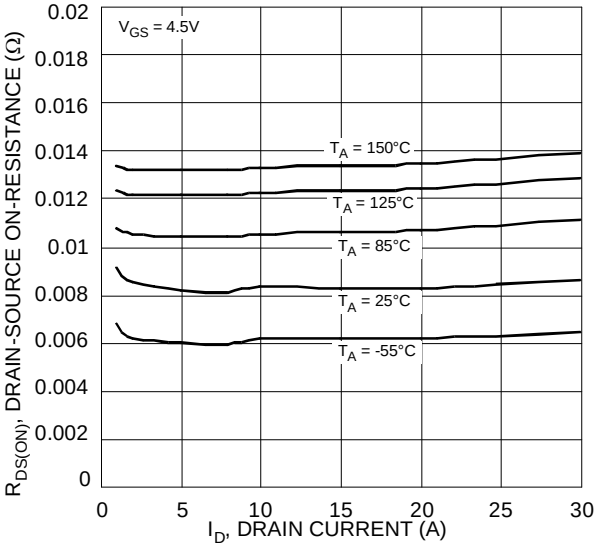


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

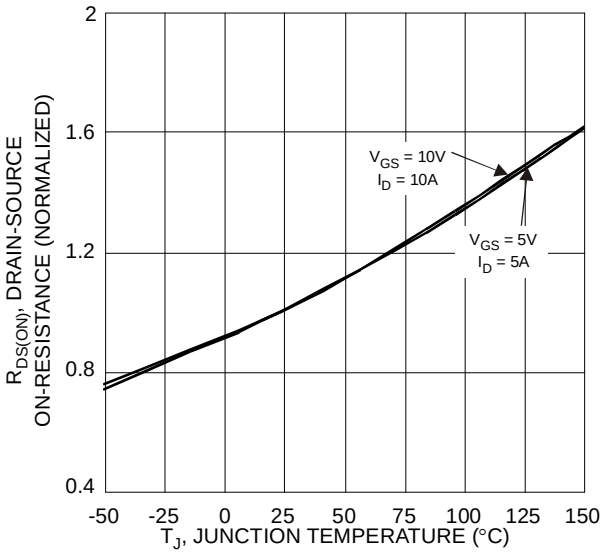


Figure 5 On-Resistance Variation with Temperature

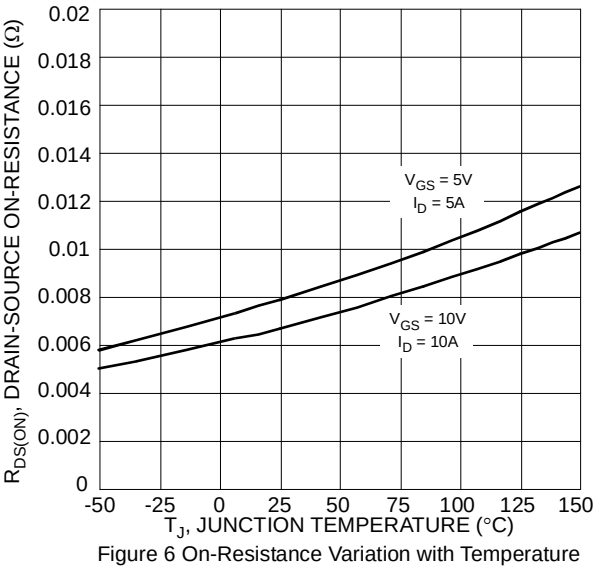


Figure 6 On-Resistance Variation with Temperature

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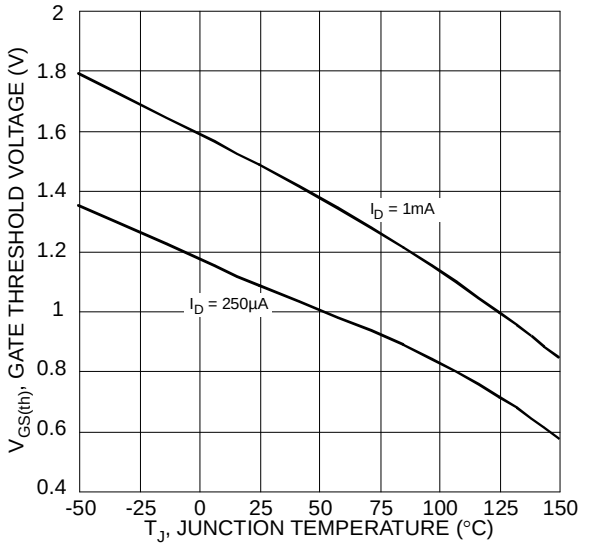


Figure 7 Gate Threshold Variation vs. Ambient Temperature

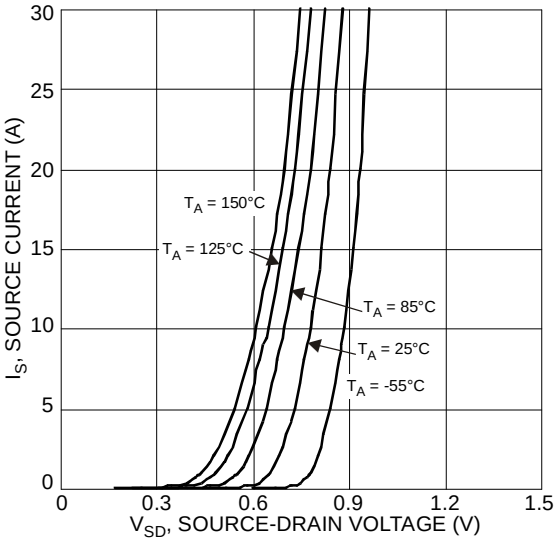


Figure 8 Diode Forward Voltage vs. Current

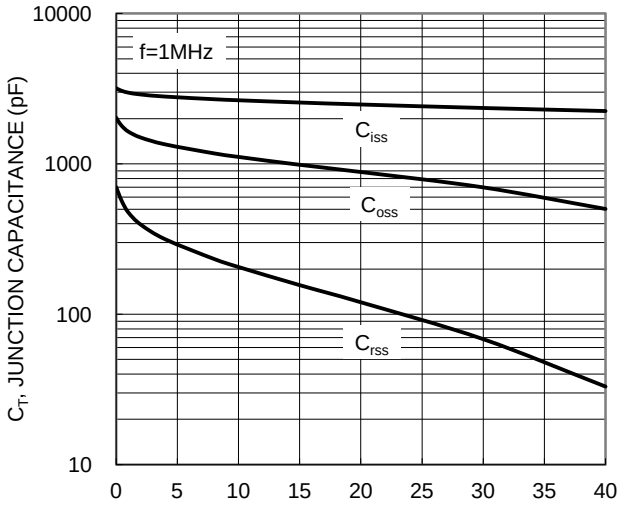


Figure 9 Typical Junction Capacitance

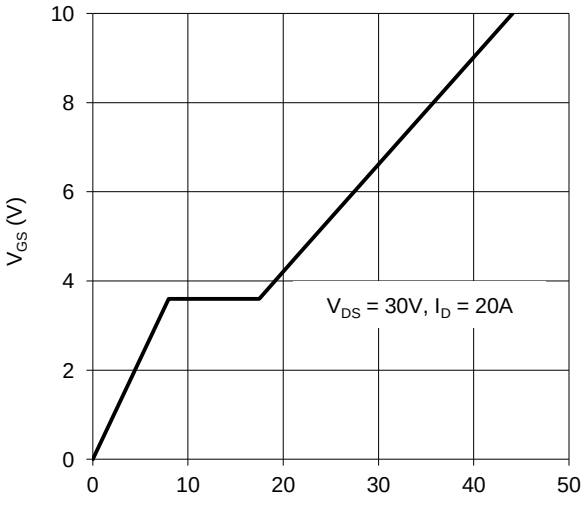


Figure 10 Gate Charge

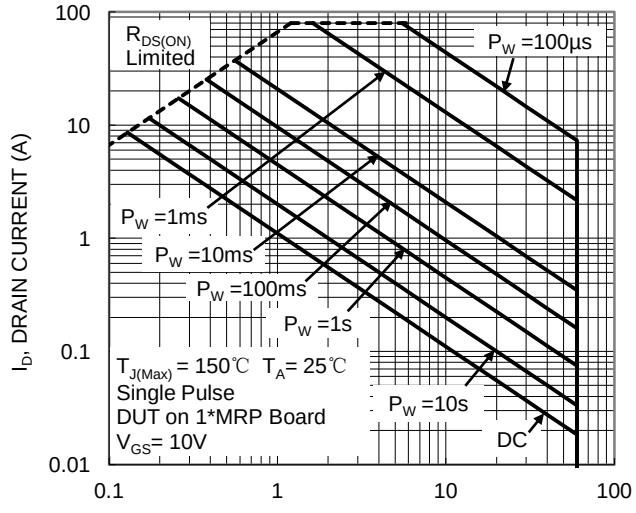


Figure 11 SOA, Safe Operation Area

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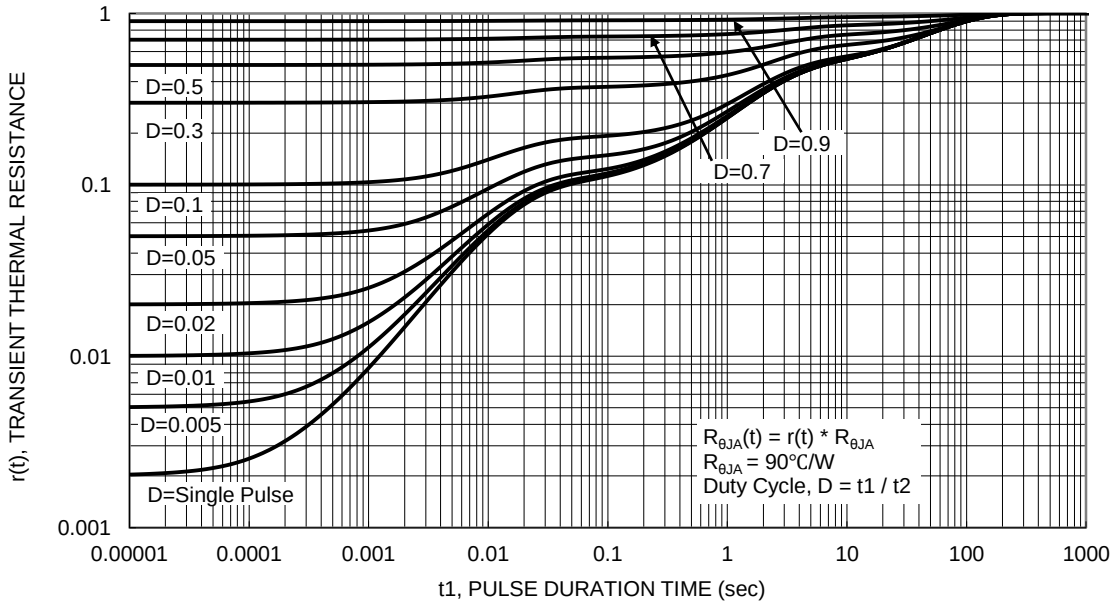


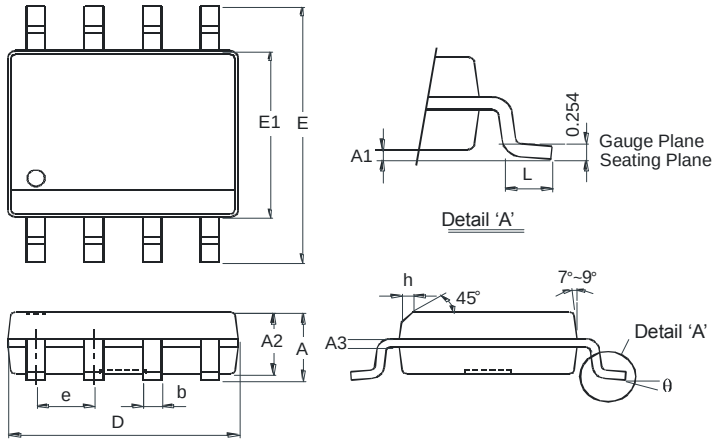
Figure 12 Transient Thermal Resistance

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Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version

SO-8

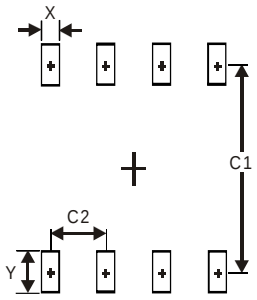


SO-8		
Dim	**Min**	**Max**
A	—	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	—	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SO-8



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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